

Kin M Yu

List of Publications by Year in descending order

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539
docs citations

539
times ranked

10985
citing authors

#	ARTICLE	IF	CITATIONS
1	Unusual properties of the fundamental band gap of InN. Applied Physics Letters, 2002, 80, 3967-3969.	1.5	1,380
2	Superior radiation resistance of In _{1-x} Ga _x N alloys: Full-solar-spectrum photovoltaic material system. Journal of Applied Physics, 2003, 94, 6477-6482.	1.1	572
3	Small band gap bowing in In _{1-x} Ga _x N alloys. Applied Physics Letters, 2002, 80, 4741-4743.	1.5	563
4	Observation of crystalline C ₃ N ₄ . Physical Review B, 1994, 49, 5034-5037.	1.1	495
5	Effect of the location of Mn sites in ferromagnetic Ga _{1-x} Mn _x As on its Curie temperature. Physical Review B, 2002, 65, .	1.1	491
6	Temperature dependence of the fundamental band gap of InN. Journal of Applied Physics, 2003, 94, 4457-4460.	1.1	375
7	Effects of the narrow band gap on the properties of InN. Physical Review B, 2002, 66, .	1.1	374
8	Valence-band anticrossing in mismatched III-V semiconductor alloys. Physical Review B, 2007, 75, .	1.1	354
9	Valence band anticrossing in Ga _{1-x} Bi _x As. Applied Physics Letters, 2007, 91, .	1.5	296
10	Engineering the Electronic Band Structure for Multiband Solar Cells. Physical Review Letters, 2011, 106, 028701.	2.9	282
11	Nature of room-temperature photoluminescence in ZnO. Applied Physics Letters, 2005, 86, 191911.	1.5	274
12	Diluted II-VI Oxide Semiconductors with Multiple Band Gaps. Physical Review Letters, 2003, 91, 246403.	2.9	268
13	Large, nitrogen-induced increase of the electron effective mass in In _y Ga _{1-y} N _x As _{1-x} . Applied Physics Letters, 2000, 76, 2409-2411.	1.5	236
14	Mechanistic insights into chemical and photochemical transformations of bismuth vanadate photoanodes. Nature Communications, 2016, 7, 12012.	5.8	231
15	Structure and electronic properties of InN and In-rich group III-nitride alloys. Journal Physics D: Applied Physics, 2006, 39, R83-R99.	1.3	229
16	Nature of the fundamental band gap in GaN _{1-x} P _x alloys. Applied Physics Letters, 2000, 76, 3251-3253.	1.5	228
17	Interaction of Localized Electronic States with the Conduction Band: Band Anticrossing in II-VI Semiconductor Ternaries. Physical Review Letters, 2000, 85, 1552-1555.	2.9	195
18	Evidence for p-Type Doping of InN. Physical Review Letters, 2006, 96, 125505.	2.9	193

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19	Fermi-level stabilization energy in group III nitrides. <i>Physical Review B</i> , 2005, 71, .	1.1	190
20	Controlling the Curie temperature in (Ga,Mn)As through location of the Fermi level within the impurity band. <i>Nature Materials</i> , 2012, 11, 444-449.	13.3	168
21	Optical properties and electronic structure of InN and In-rich group III-nitride alloys. <i>Journal of Crystal Growth</i> , 2004, 269, 119-127.	0.7	157
22	Ni, Pd, and Pt on GaAs: A comparative study of interfacial structures, compositions, and reacted film morphologies. <i>Journal of Materials Research</i> , 1987, 2, 262-275.	1.2	149
23	Effect of vacuum arc deposition parameters on the properties of amorphous carbon thin films. <i>Surface and Coatings Technology</i> , 1994, 68-69, 388-393.	2.2	132
24	Novel metal ion surface modification technique. <i>Applied Physics Letters</i> , 1991, 58, 1392-1394.	1.5	129
25	Multiband GaNAsP quaternary alloys. <i>Applied Physics Letters</i> , 2006, 88, 092110.	1.5	128
26	Breakdown of crystallinity in low-temperature-grown GaAs layers. <i>Applied Physics Letters</i> , 1991, 58, 2153-2155.	1.5	125
27	Band Anticrossing in III-N-V Alloys. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 223, 75-85.	0.7	119
28	Dependence of the fundamental band gap of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ on alloy composition and pressure. <i>Journal of Applied Physics</i> , 1999, 85, 8505-8507.	1.1	112
29	Two-photon excitation in an intermediate band solar cell structure. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	110
30	A comparative study of phase stability and film morphology in thin-film M/GaAs systems (M=Co, Rh, Ir). <i>Tj ETQq0 0,0 rgBT /Overlock 106</i>	1.1	106
31	Universal bandgap bowing in group-III nitride alloys. <i>Solid State Communications</i> , 2003, 127, 411-414.	0.9	104
32	On the macroparticle flux from vacuum arc cathode spots. <i>IEEE Transactions on Plasma Science</i> , 1993, 21, 440-446.	0.6	103
33	On the crystalline structure, stoichiometry and band gap of InN thin films. <i>Applied Physics Letters</i> , 2005, 86, 071910.	1.5	103
34	Reduction of band-gap energy in GaNAs and AlGaAs synthesized by N ⁺ implantation. <i>Applied Physics Letters</i> , 1999, 75, 1410-1412.	1.5	102
35	Effect of nitrogen on the electronic band structure of group III-N-V alloys. <i>Physical Review B</i> , 2000, 62, 4211-4214.	1.1	101
36	Simultaneous Enhancement of Electrical Conductivity and Thermopower of $\text{Bi}_{2-x}\text{Te}_{3-x}$ by Multifunctionality of Native Defects. <i>Advanced Materials</i> , 2015, 27, 3681-3686.	11.1	97

#	ARTICLE	IF	CITATIONS
37	Ferromagnetism in $\text{Ga}_{1-x}\text{MnxP}$: Evidence for Inter-Mn Exchange Mediated by Localized Holes within a Detached Impurity Band. <i>Physical Review Letters</i> , 2005, 95, 207204.	2.9	92
38	Large kinetic asymmetry in the metal-insulator transition nucleated at localized and extended defects. <i>Physical Review B</i> , 2011, 83, .	1.1	92
39	Highly Uniform and Stable n-Type Carbon Nanotube Transistors by Using Positively Charged Silicon Nitride Thin Films. <i>Nano Letters</i> , 2015, 15, 392-397.	4.5	92
40	Curie temperature limit in ferromagnetic $\text{Ga}_{1-x}\text{MnxAs}$. <i>Physical Review B</i> , 2003, 68, .	1.1	91
41	On-Nanowire Axial Heterojunction Design for High-Performance Photodetectors. <i>ACS Nano</i> , 2016, 10, 8474-8481.	7.3	88
42	Characterization of GaAs layers grown by low temperature molecular beam epitaxy using ion beam techniques. <i>Journal of Applied Physics</i> , 1992, 72, 2850-2856.	1.1	87
43	Existence and removal of Cu_2Se second phase in coevaporated $\text{Cu}_2\text{ZnSnSe}_4$ thin films. <i>Journal of Applied Physics</i> , 2012, 111, .	1.1	87
44	Ferromagnetic $\text{Ga}_{1-x}\text{MnxAs}$ produced by ion implantation and pulsed-laser melting. <i>Applied Physics Letters</i> , 2003, 82, 1251-1253.	1.5	86
45	Valence band hybridization in N-rich $\text{Ga}_{1-x}\text{As}_x$ alloys. <i>Physical Review B</i> , 2004, 70, .	1.1	86
46	Ideal transparent conductors for full spectrum photovoltaics. <i>Journal of Applied Physics</i> , 2012, 111, .	1.1	86
47	Growth and properties of GaSbBi alloys. <i>Applied Physics Letters</i> , 2013, 103, 142106.	1.5	84
48	Plasma synthesis of metallic and composite thin films with atomically mixed substrate bonding. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1993, 80-81, 1281-1287.	0.6	83
49	Effect of band anticrossing on the optical transitions in $\text{GaAs}_{1-x}\text{Nx}/\text{GaAs}$ multiple quantum wells. <i>Physical Review B</i> , 2001, 64, .	1.1	83
50	Pressure-dependent photoluminescence study of ZnO nanowires. <i>Applied Physics Letters</i> , 2005, 86, 153117.	1.5	83
51	Synthesis and optical properties of II-O-VI highly mismatched alloys. <i>Journal of Applied Physics</i> , 2004, 95, 6232-6238.	1.1	82
52	Effect of oxygen on the electronic band structure in ZnOxSe_{1-x} alloys. <i>Applied Physics Letters</i> , 2003, 83, 299-301.	1.5	76
53	$\text{In}_{1-x}\text{MnxSb}_x$ a narrow-gap ferromagnetic semiconductor. <i>Applied Physics Letters</i> , 2003, 82, 4310-4312.	1.5	71
54	Enhancement of Curie temperature in $\text{Ga}_{1-x}\text{MnxAs}/\text{Ga}_{1-y}\text{AlyAs}$ ferromagnetic heterostructures by Be modulation doping. <i>Applied Physics Letters</i> , 2003, 83, 4220-4222.	1.5	70

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55	Pressure dependence of the fundamental band-gap energy of CdSe. Applied Physics Letters, 2004, 84, 67-69.	1.5	70
56	High Bi content GaSbBi alloys. Journal of Applied Physics, 2014, 116, .	1.1	70
57	Band anticrossing in GaP _{1-x} N _x alloys. Physical Review B, 2002, 65, .	1.1	67
58	Origin of the large band-gap bowing in highly mismatched semiconductor alloys. Physical Review B, 2003, 67, .	1.1	67
59	Band gap bowing parameter of In _{1-x} Al _x N. Journal of Applied Physics, 2008, 104, .	1.1	67
60	Hole transport and photoluminescence in Mg-doped InN. Journal of Applied Physics, 2010, 107, .	1.1	67
61	Band anticrossing in highly mismatched Sn _x Ge _{1-x} alloys. Physical Review B, 2008, 77, .	1.1	66
62	Fermi level stabilization energy in cadmium oxide. Journal of Applied Physics, 2010, 107, .	1.1	66
63	Nitrogen-induced increase of the maximum electron concentration in group III-N-V alloys. Physical Review B, 2000, 61, R13337-R13340.	1.1	65
64	Demonstration of a III-Nitride/Silicon Tandem Solar Cell. Applied Physics Express, 2009, 2, 122202.	1.1	64
65	Effects of surface states on electrical characteristics of InN and In _{1-x} Ga _x N. Physical Review B, 2007, 76, .	1.1	61
66	Highly mismatched crystalline and amorphous GaN _{1-x} As _x alloys in the whole composition range. Journal of Applied Physics, 2009, 106, .	1.1	61
67	Photocurrent induced by two-photon excitation in ZnTeO intermediate band solar cells. Applied Physics Letters, 2013, 102, .	1.5	61
68	Molecular beam epitaxial growth and optical properties of highly mismatched ZnTe _{1-x} O _x alloys. Applied Physics Letters, 2012, 100, .	1.5	60
69	Crystal structure and properties of Cd _x Zn _{1-x} O alloys across the full composition range. Applied Physics Letters, 2013, 102, .	1.5	60
70	Self-Densified Optically Transparent VO ₂ Thermo-chromic Wood Film for Smart Windows. ACS Applied Materials & Interfaces, 2021, 13, 22495-22504.	4.0	60
71	Structural analysis of ferromagnetic Mn-doped ZnO thin films deposited by radio frequency magnetron sputtering. Journal of Applied Physics, 2005, 97, 126107.	1.1	59
72	Effect of charged dislocation scattering on electrical and electrothermal transport in n-type InN. Physical Review B, 2011, 84, .	1.1	59

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73	Structural and optical quality of GaN/metal/Si heterostructures fabricated by excimer laser lift-off. Applied Physics Letters, 1999, 75, 1887-1889.	1.5	57
74	Band structure engineering of ZnO \hat{x} Sex alloys. Applied Physics Letters, 2010, 97, .	1.5	56
75	Mutual passivation of electrically active and isovalent impurities. Nature Materials, 2002, 1, 185-189.	13.3	55
76	Mg \hat{e} doped InN and InGaN \hat{e} Photoluminescence, capacitance \hat{e} voltage and thermopower measurements. Physica Status Solidi (B): Basic Research, 2008, 245, 873-877.	0.7	55
77	Ion-dose-dependent microstructure in amorphous Ge. Physical Review B, 2000, 61, 12586-12589.	1.1	54
78	Effects of Free Carriers on the Optical Properties of Doped CdO for Full-Spectrum Photovoltaics. Physical Review Applied, 2016, 6, .	1.5	54
79	Mechanism of stress relaxation in Ge nanocrystals embedded in SiO ₂ . Applied Physics Letters, 2005, 86, 063107.	1.5	52
80	Electron mobility in InN and III-N alloys. Journal of Applied Physics, 2007, 102, 073705.	1.1	52
81	Universal and Solution-Processable Precursor to Bismuth Chalcogenide Thermoelectrics. Chemistry of Materials, 2010, 22, 1943-1945.	3.2	52
82	Formation of Mn-derived impurity band in III-Mn-V alloys by valence band anticrossing. Physical Review B, 2008, 78, .	1.1	50
83	Theoretical and experimental studies of electronic band structure for GaSb \hat{x} Bix in the dilute Bi regime. Journal Physics D: Applied Physics, 2014, 47, 355107.	1.3	50
84	Organic Hybrid Perovskite (MAPbI ₃ \hat{x} Cl _x) for Thermochromic Smart Window with Strong Optical Regulation Ability, Low Transition Temperature, and Narrow Hysteresis Width. Advanced Functional Materials, 2021, 31, 2010426.	7.8	50
85	Structure-Dependent Hydrostatic Deformation Potentials of Individual Single-Walled Carbon Nanotubes. Physical Review Letters, 2004, 93, .	2.9	49
86	Growth of II \hat{e} VI thin films from single-source precursors based on sterically encumbered sited ligands. Journal of Crystal Growth, 1992, 124, 647-653.	0.7	48
87	Determination of free hole concentration in ferromagnetic Ga \hat{x} MnxAs using electrochemical capacitance \hat{e} voltage profiling. Applied Physics Letters, 2002, 81, 844-846.	1.5	48
88	Synthesis of GaNxAs \hat{x} thin films by pulsed laser melting and rapid thermal annealing of N $\hat{+}$ -implanted GaAs. Journal of Applied Physics, 2003, 94, 1043-1049.	1.1	48
89	Structural and electronic properties of amorphous and polycrystalline In ₂ Se ₃ films. Journal of Applied Physics, 2003, 94, 2390-2397.	1.1	48
90	High quality ZnO:Al transparent conducting oxide films synthesized by pulsed filtered cathodic arc deposition. Thin Solid Films, 2010, 518, 3313-3319.	0.8	48

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91	Bi-induced band gap reduction in epitaxial InSbBi alloys. Applied Physics Letters, 2014, 105, .	1.5	48
92	Metalorganic Chemical Vapor Deposition of Semiconducting III/VI In ₂ Se ₃ Thin Films from the Single-Source Precursor: In[SeC(SiMe ₃) ₃] ₃ . Chemistry of Materials, 1995, 7, 2273-2276.	3.2	47
93	High temperature behavior of Pt and Pd on GaN. Journal of Applied Physics, 1997, 81, 3134-3137.	1.1	47
94	Electrical activation and electron spin resonance measurements of implanted bismuth in isotopically enriched silicon-28. Applied Physics Letters, 2012, 100, .	1.5	47
95	Room-temperature Red "Green" Blue Whispering Gallery Mode Lasing and White Light Emission from Cesium Lead Halide Perovskite (CsPbX ₃ , X = Cl, Br, I) Microstructures. Advanced Optical Materials, 2018, 6, 1700993.	3.6	47
96	Synthesis of In _{Nx} P _{1-x} thin films by N ion implantation. Applied Physics Letters, 2001, 78, 1077-1079.	1.5	46
97	Electronic structure of $Ga_{1-x}P_x$ according to hole-concentration-dependent measurements. Physical Review B, 2010, 81, .	1.5	46
98	Temperature dependence of the band gap of GaSb _{1-x} Bi _x alloys with $\alpha = 0.042$ determined by photorefectance. Applied Physics Letters, 2013, 103, .	1.5	46
99	Characterization of the local structure of amorphous GaAs produced by ion implantation. Journal of Applied Physics, 1998, 83, 4610-4614.	1.1	45
100	Fermi-level stabilization in the topological insulators Bi_2Se_3 and Bi_2Te_3 . Physical Review B, 2014, 89, .	1.5	45
101	Mg doped InN and confirmation of free holes in InN. Applied Physics Letters, 2011, 98, 042104.	1.5	44
102	Growth and characterization of ZnO _{1-x} S _x highly mismatched alloys over the entire composition. Journal of Applied Physics, 2015, 118, .	1.1	43
103	Schottky barrier degradation of the W/GaAs system after high-temperature annealing. Journal of Applied Physics, 1986, 60, 3235-3242.	1.1	42
104	Formation of diluted III-V nitride thin films by N ion implantation. Journal of Applied Physics, 2001, 90, 2227-2234.	1.1	42
105	Compensating point defects in He ⁺ -irradiated InN. Physical Review B, 2007, 75, .	1.1	42
106	Effects of point defects on thermal and thermoelectric properties of InN. Applied Physics Letters, 2011, 98, .	1.5	42
107	Vacancy defects induced changes in the electronic and optical properties of NiO studied by spectroscopic ellipsometry and first-principles calculations. Journal of Applied Physics, 2020, 128, .	1.1	42
108	Demonstration of homojunction ZnTe solar cells. Journal of Applied Physics, 2010, 108, .	1.1	40

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109	Composition-dependent bond lengths in crystalline and amorphized $GexSi_{1-x}$ alloys. Physical Review B, 1999, 60, 10831-10836.	1.1	39
110	Crystalline all-inorganic lead-free $Cs_3Sb_2I_9$ perovskite microplates with ultra-fast photoconductive response and robust thermal stability. Nano Research, 2021, 14, 4116-4124.	5.8	39
111	Band-gap bowing effects in $BxGa_{1-x}As$ alloys. Journal of Applied Physics, 2003, 93, 2696-2699.	1.1	38
112	Stable, freestanding Ge nanocrystals. Journal of Applied Physics, 2005, 97, 124316.	1.1	38
113	Demonstration of $ZnTe_{1-x}O_x$ Intermediate Band Solar Cell. Japanese Journal of Applied Physics, 2011, 50, 082304.	0.8	37
114	GaNAsP: An intermediate band semiconductor grown by gas-source molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	1.5	37
115	Fermi level stabilization and band edge energies in $CdxZn_{1-x}O$ alloys. Journal of Applied Physics, 2014, 115, .	1.1	37
116	Near-Infrared-Activated Thermochromic Perovskite Smart Windows. Advanced Science, 2022, 9, e2106090.	5.6	37
117	Lattice location of diffused Zn atoms in GaAs and InP single crystals. Journal of Applied Physics, 1991, 69, 2998-3006.	1.1	36
118	Optimization of Ge/C ratio for compensation of misfit strain in solid phase epitaxial growth of SiGe layers. Applied Physics Letters, 1993, 63, 2682-2684.	1.5	36
119	Growth and properties of ferromagnetic $In_{1-x}Mn_xSb$ alloys. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 20, 325-332.	1.3	36
120	Characterization of low-temperature molecular-beam-epitaxy grown GaBiAs layers. Semiconductor Science and Technology, 2007, 22, 819-823.	1.0	36
121	Full multiple scattering analysis of XANES at the $Cd_{1-x}L_x$ in CdO films combined with a soft-x-ray emission investigation. Physical Review B, 2010, 82, .	1.1	36
122	Coimplantation and electrical activity of C in GaAs: Stoichiometry and damage effects. Applied Physics Letters, 1992, 60, 2383-2385.	1.5	35
123	Band anticrossing in dilute nitrides. Journal of Physics Condensed Matter, 2004, 16, S3355-S3372.	0.7	34
124	Metal-Insulator Transition by Isovalent Anion Substitution in $Ga_{1-x}MnxAs$: Implications to Ferromagnetism. Physical Review Letters, 2008, 101, 087203.	2.9	34
125	Synthesis of GaN nanocrystals by sequential ion implantation. Applied Physics Letters, 1997, 70, 2268-2270.	1.5	33
126	High-temperature Hall effect in $Ga_{1-x}MnxAs$. Physical Review B, 2004, 69, .	1.1	33

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127	GaN _{1-x} Bi _x : Extremely mismatched semiconductor alloys. Applied Physics Letters, 2010, 97, 141919.	1.5	33
128	Self-generated oscillations in continuous crystallizers: Part I. Analytical prediction of the oscillating output. AIChE Journal, 1975, 21, 917-924.	1.8	32
129	High-temperature annealing characteristics of tungsten and tungsten nitride Schottky contacts to GaAs under different annealing conditions. Journal of Applied Physics, 1988, 64, 1284-1291.	1.1	32
130	Defects and properties of cadmium oxide based transparent conductors. Journal of Applied Physics, 2016, 119, .	1.1	32
131	Band anticrossing in group II-VI highly mismatched alloys: Cd _{1-x} Mn _y O _x Te _{1-x} quaternaries synthesized by O ion implantation. Applied Physics Letters, 2002, 80, 1571-1573.	1.5	31
132	Effects of rapid quenching on the impurity site location in Zn-diffused InP. Journal of Applied Physics, 1993, 74, 86-90.	1.1	30
133	Reduction of threading dislocation density in GaN using an intermediate temperature interlayer. Applied Physics Letters, 2000, 77, 3562-3564.	1.5	30
134	Nitrogen-induced enhancement of the free electron concentration in sulfur implanted GaN _x As _{1-x} . Applied Physics Letters, 2000, 77, 2858-2860.	1.5	29
135	Effect of film thickness on the incorporation of Mn interstitials in Ga _{1-x} Mn _x As. Applied Physics Letters, 2005, 86, 042102.	1.5	29
136	Doping and defect control of ferromagnetic semiconductors formed by ion implantation and pulsed-laser melting. Physica B: Condensed Matter, 2006, 376-377, 630-634.	1.3	29
137	High electron mobility InN. Applied Physics Letters, 2007, 90, 162103.	1.5	29
138	Electrical transport and ferromagnetism in Ga _{1-x} Mn _x As synthesized by ion implantation and pulsed-laser melting. Journal of Applied Physics, 2008, 103, 073913.	1.1	29
139	Effect of Sb on GaNAs Intermediate Band Solar Cells. IEEE Journal of Photovoltaics, 2013, 3, 730-736.	1.5	29
140	Enhanced nitrogen incorporation by pulsed laser annealing of GaN _x As _{1-x} formed by N ion implantation. Applied Physics Letters, 2002, 80, 3958-3960.	1.5	28
141	Cross-section transmission electron microscopy study of carbon-implanted layers in silicon. Applied Physics Letters, 1990, 57, 798-800.	1.5	27
142	Electronic effects determining the formation of ferromagnetic III _{1-x} Mn _x V alloys during epitaxial growth. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 25, 171-180.	1.3	27
143	Mn _{L2,3} x-ray absorption and magnetic circular dichroism in ferromagnetic Ga _{1-x} Mn _x P. Applied Physics Letters, 2006, 89, 012504.	1.5	27
144	Embedded Binary Eutectic Alloy Nanostructures: A New Class of Phase Change Materials. Nano Letters, 2010, 10, 2794-2798.	4.5	27

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145	Electronic band structure of ZnO-rich highly mismatched ZnO $_{1-x}$ Te $_x$ alloys. Applied Physics Letters, 2015, 106, .	1.5	27
146	Bi flux-dependent MBE growth of GaSbBi alloys. Journal of Crystal Growth, 2015, 425, 241-244.	0.7	27
147	Structural characterization of low-temperature molecular beam epitaxial In $_{0.52}$ Al $_{0.48}$ As/InP heterolayers. Applied Physics Letters, 1992, 60, 989-991.	1.5	26
148	Highly mismatched N-rich GaN $_{1-x}$ Sb $_x$ films grown by low temperature molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	1.5	26
149	Charge transfer and mobility enhancement at CdO/SnTe heterointerfaces. Applied Physics Letters, 2014, 105, 132103.	1.5	26
150	Rapid thermal annealing assisted facile solution method for tungsten-doped vanadium dioxide thin films on glass substrate. Journal of Alloys and Compounds, 2020, 833, 155053.	2.8	26
151	Structural-relaxation-induced bond length and bond angle changes in amorphized Ge. Physical Review B, 2001, 63, .	1.1	25
152	Diluted magnetic semiconductors formed by ion implantation and pulsed-laser melting. Physica B: Condensed Matter, 2003, 340-342, 908-912.	1.3	25
153	Narrow bandgap group III-nitride alloys. Physica Status Solidi (B): Basic Research, 2003, 240, 412-416.	0.7	25
154	Diluted ZnMnTe oxide: a multi-band semiconductor for high efficiency solar cells. Physica Status Solidi (B): Basic Research, 2004, 241, 660-663.	0.7	25
155	Electrical properties of InGaN ϵ Si heterojunctions. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S413.	0.8	25
156	Electronic structure of CdO studied by soft X-ray spectroscopy. Journal of Electron Spectroscopy and Related Phenomena, 2011, 184, 249-253.	0.8	25
157	Photogenerated Current By Two-Step Photon Excitation in ZnTeO Intermediate Band Solar Cells with n-ZnO Window Layer. IEEE Journal of Photovoltaics, 2014, 4, 196-201.	1.5	25
158	Electronic band structure of highly mismatched GaN $_{1-x}$ Sb $_x$ alloys in a broad composition range. Applied Physics Letters, 2015, 107, .	1.5	25
159	Band structure of germanium carbides for direct bandgap silicon photonics. Journal of Applied Physics, 2016, 120, .	1.1	25
160	Effects of interface reactions on electrical characteristics of metal ϵ GaAs contacts. Applied Physics Letters, 1987, 51, 189-191.	1.5	24
161	Solid-phase reactions between (100) GaAs and thin-film refractory metals (Ti, Zr, V, Nb, Cr, Mo, and W). Applied Physics A: Solids and Surfaces, 1987, 44, 177-190.	1.4	24
162	Lattice site locations of excess arsenic atoms in gallium arsenide grown by low-temperature molecular beam epitaxy. Applied Physics Letters, 1991, 59, 3267-3269.	1.5	24

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163	Native-defect-controlled n-type conductivity in InN. <i>Physica B: Condensed Matter</i> , 2006, 376-377, 436-439.	1.3	24
164	Self-Passivation of Defects: Effects of High-Energy Particle Irradiation on the Elastic Modulus of Multilayer Graphene. <i>Advanced Materials</i> , 2015, 27, 6841-6847.	11.1	24
165	Room-Temperature-Synthesized High-Mobility Transparent Amorphous CdO ₂ Ga ₂ O ₃ Alloys with Widely Tunable Electronic Bands. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 7239-7247.	4.0	24
166	Strain-engineered ferromagnetic In _{1-x} MnxAs films with in-plane easy axis. <i>Applied Physics Letters</i> , 2005, 86, 112512.	1.5	23
167	p-type InN and In-rich InGaN. <i>Physica Status Solidi (B): Basic Research</i> , 2007, 244, 1820-1824.	0.7	23
168	Structural properties of Ge nanocrystals embedded in sapphire. <i>Journal of Applied Physics</i> , 2006, 100, 114317.	1.1	22
169	Molecular beam epitaxy of crystalline and amorphous GaN layers with high As content. <i>Journal of Crystal Growth</i> , 2009, 311, 3417-3422.	0.7	22
170	Increasing the retained dose by plasma immersion ion implantation and deposition. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1995, 102, 132-135.	0.6	21
171	Multiphonon resonance Raman scattering in In _x Ga _{1-x} N. <i>Physical Review B</i> , 2005, 72, .	1.1	21
172	Compositional modulation in In _x Ga _{1-x} N: TEM and X-ray studies. <i>Microscopy (Oxford, England)</i> , 2005, 54, 243-250.	0.7	21
173	Material properties of Cd _{1-x} Mg _x O alloys synthesized by radio frequency sputtering. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	21
174	Potential building energy savings by passive strategies combining daytime radiative coolers and thermochromic smart windows. <i>Case Studies in Thermal Engineering</i> , 2021, 28, 101517.	2.8	21
175	Common structure in amorphised compound semiconductors. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2003, 199, 235-239.	0.6	20
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